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(54) SOLID-STATE IMAGING DEVICE AND METHOD OF MANUFACTURING SOLID-STATE IMAGING DEVICE

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(57) ABSTRACT

A solid-state imaging device includes a photoelectric conversion element. The photoelectric conversion element includes a first electrode, an electron transport layer, and a photoelectric conversion layer. The first electrode is disposed on a substrate and the photoelectric conversion layer is disposed on the first electrode. The electron transport layer is disposed between the first electrode and the photoelectric conversion layer and includes a buffer layer and a particulate layer. The buffer layer has an ionization potential larger than a work function of the first electrode and an electron affinity larger than the photoelectric conversion layer. Then, the particulate layer includes particulates that contain conductive zinc oxide as a main component.